Abstracts

Self-Consistent FET Models for Amplifier Design and Device Diagnostics

W.R. Curtice and R.L. Camisa. "Self-Consistent FET Models for Amplifier Design and Device Diagnostics." 1984 MTT-S International Microwave Symposium Digest 84.1 (1984 [MWSYM]): 427-429.

A procedure has been developed for producing accurate and unique equivalent circuit models for carrier mounted GaAs FETs. The procedure incorporates zero drain-source bias S-parameter tests as well as Fukui-type, dc measurements. Data for 1 µm gate length, 600 µm periphery GaAs FETs are presented.

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